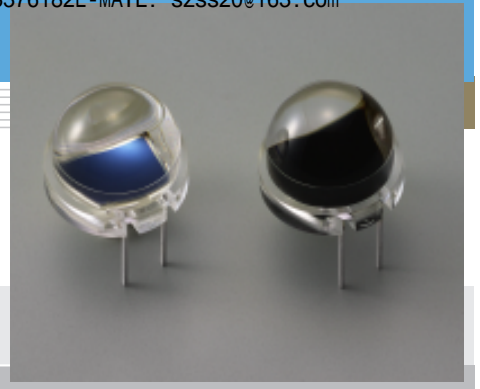


## PHOTODIODE

# Si PIN photodiode

## S6801/S6968 series

φ14 mm lens plastic package



S6801/S6968 series is a Si PIN photodiode molded into a plastic package with a φ14 mm lens. Four types are provided, S6801, S6968 with a clear plastic package and S6801-01, S6968-01 with a visible-cut package.

### Features

- Plastic packages with φ14 mm lens
- High-speed response (S6968 series): 50 MHz Typ. ( $V_R=10\text{ V}$ ,  $\lambda=850\text{ nm}$ )
- High sensitivity (S6801, S6968): 0.63 A/W ( $\lambda=850\text{ nm}$ )
- Directivity: 35° (half angle)
- Visible-cut type: S6801-01, S6968-01
- Active area size: φ14 mm (lens diameter)
- Effective active area: 150 mm<sup>2</sup>

### Applications

- Spatial light transmission
- Optical communication
- Optical data link
- High-speed optical measurement
- Optical switch
- Laser radar

### General ratings / Absolute maximum ratings

Type No.	Package	Active area size (mm)	Effective active area (mm <sup>2</sup> )	Absolute maximum ratings		
				Reverse voltage $V_R$ Max. (V)	Operating temperature $T_{opr}$ (°C)	Storage temperature $T_{stg}$ (°C)
S6801	Plastic	φ14	150	35	-25 to +85	-40 to +100
S6801-01						
S6968						
S6968-01						

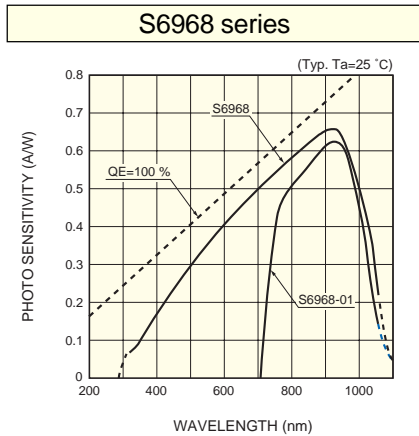
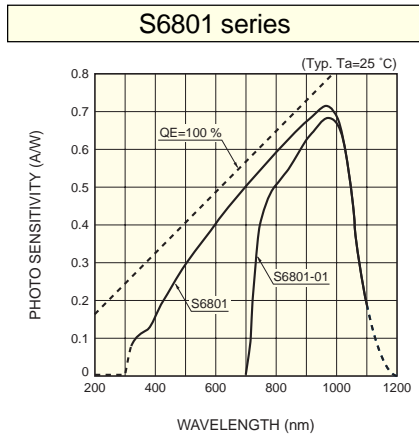
### Electrical and optical characteristics

Type No.	Spectral response range $\lambda$ (nm)	Peak sensitivity wavelength $\lambda_p$ (nm)	Photo sensitivity S $\lambda=850\text{ nm}$		Short circuit current $I_{sc}$ 100 $\mu\text{A}$ 2856 K		Dark current $I_D$ $V_R=10\text{ V}$		Temp. coefficient of $I_D$ $T_{CID}$ (times/°C)	Cut-off frequency $f_c$ $V_R=10\text{ V}$ $R_L=50\ \Omega$ $\lambda=850\text{ nm}$ , -3 dB		Terminal capacitance $C_t$ $V_R=10\text{ V}$ $f=1\text{ MHz}$		Half * angle (degree)
			Min. (A/W)	Typ. (A/W)	Min. ( $\mu\text{A}$ )	Typ. ( $\mu\text{A}$ )	Typ. (nA)	Max. (nA)		Min. (MHz)	Typ. (MHz)	Typ. (pF)	Max. (pF)	
S6801	320 to 1100	960	0.57	0.63	95	120	0.5	10	1.15	7	15	40	80	±35
S6801-01	700 to 1100		0.5	0.55	64	80								
S6968	320 to 1060	920	0.57	0.63	83	104	0.5	5		30	50	50	100	
S6968-01	700 to 1060		0.5	0.55	57	72								

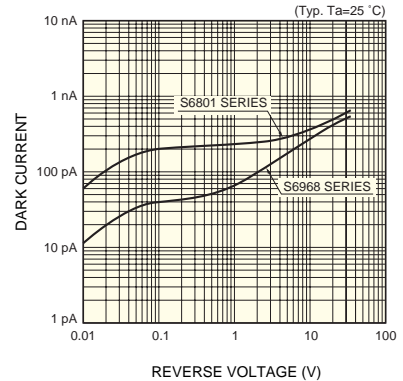
\* Photocurrent generated in a photodiode varies depending on the incident light angle. The half angle is the incident light angle at which the photocurrent is 50 % of that generated when the incident light is perpendicular to the photodiode.

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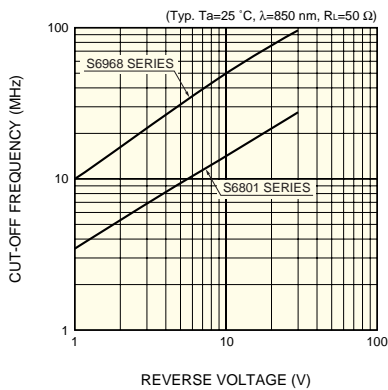
■ Spectral response



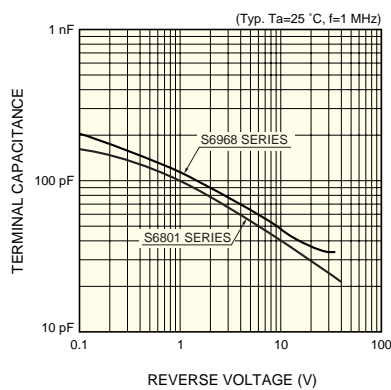
■ Dark current vs. reverse voltage



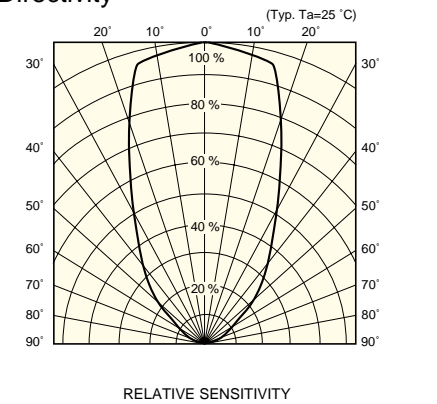
■ Cut-off frequency vs. reverse voltage



■ Terminal capacitance vs. reverse voltage

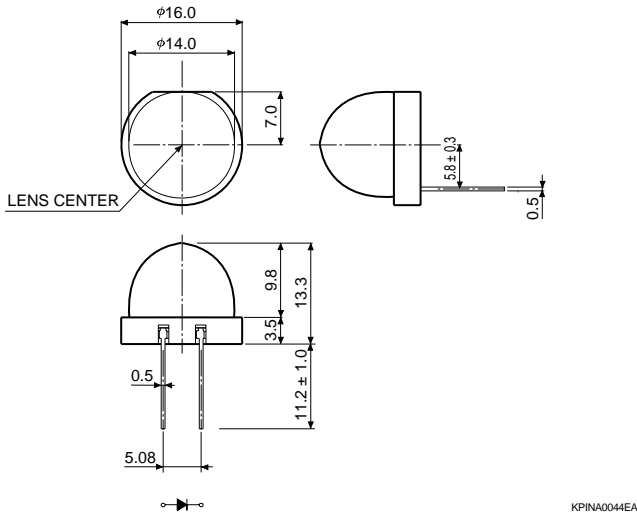


■ Directivity



■ Dimensional outline

(unit: mm, tolerance unless otherwise noted: ±0.1)



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